

RF AMPLIFIER

MODEL *TM6153*

Available as: TM6153, 4 Pin TO-8 (T4)
 TN6153-3, 4 Pin Surface Mount (SM3)
 FP6153-4, 4 Pin Flatpack (FP4)
 BX6153, Connectorized Housing (H1)
 PN6153, Reduced Size Surface Mount (SM11)

Features

- GaAs FET: Low Noise Figure: <3 dB Typical
- Medium Output Power: >+7 dBm Typical
- Operating Case Temp. -55 °C to + 85°C
- Environmental Screening Available

Specifications

CHARACTERISTIC	TYPICAL Ta= 25 °C	MIN/MAX Ta = -55 °C to +85 °C
Frequency	300-1800 MHz	300-1800 MHz
Gain (dB)	11.5	10.5 Min.
Power @ 1 dB Comp. (dBm)	> +7	+6.0 Min.
Reverse Isolation (dB)	- 17	-15 Max.
VSWR In	<2.5:1	3.0:1 Max.
VSWR Out	<2.0:1	2.5:1 Max.
Noise figure (dB)	<3	4.0 Max.
Power Vdc	+15	+15
mA	18	20 Max.

Note: Care should always be taken to effectively ground the case of each unit.

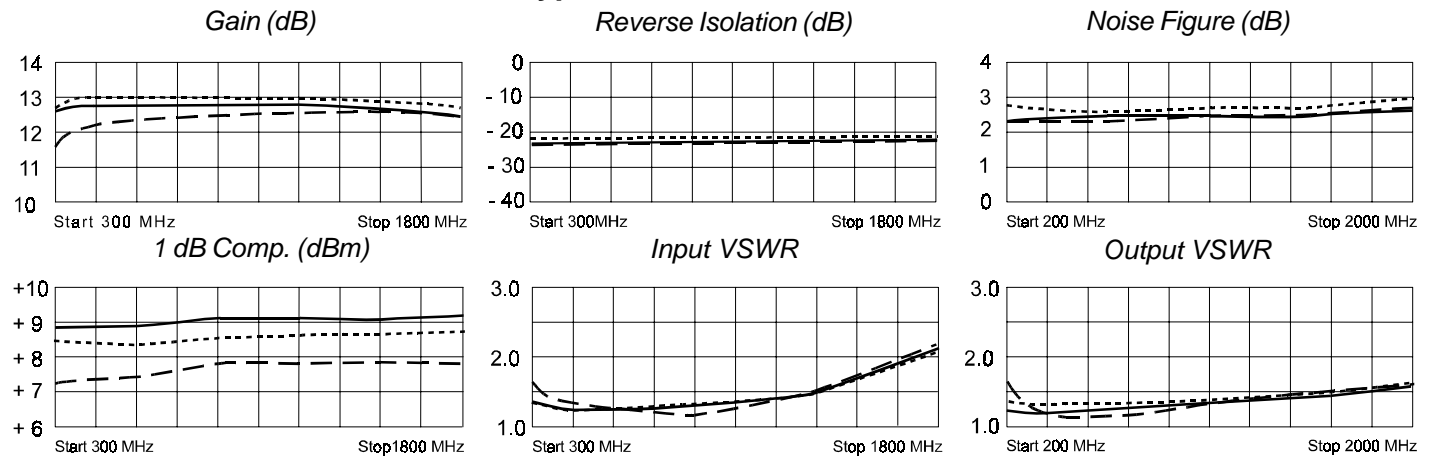
Typical Intermodulation Performance at 25 ° C

Second Order Harmonic Intercept Point +28 (Typ.)
 Second Order Two Tone Intercept Point +22 (Typ.)
 Third Order Two Tone Intercept Point +18 (Typ.)

Maximum Ratings

Ambient Operating Temperature -55°C to + 100 °C
 Storage Temperature -62°C to + 125 °C
 Case Temperature + 125 °C
 DC Voltage + 18 Volts
 Continuous RF Input Power + 10 dBm
 Short Term RF Input Power 50 Milliwatts
 (1 Minute Max.)
 Maximum Peak Power 0.5 Watt
 (3 µsec Max.)

Typical Performance Data



Legend ——— + 25 °C - - - - + 85 °C ······ -55 °C

Linear S-Parameters

FREQ. MHz	S11		S21		S12		S22	
	Mag	Deg	Mag	Deg	Mag	Deg	Mag	Deg
300	.27	-41	3.83	148	.11	-14	.05	25
400	.29	-53	3.79	138	.11	-19	.06	12
600	.33	-76	3.74	117	.11	-30	.07	-15
800	.38	-96	3.67	97	.11	-40	.06	-36
1000	.39	-117	3.72	78	.11	-49	.07	-41
1400	.38	-137	3.83	56	.12	-60	.06	-58
1600	.32	-163	4.02	31	.12	-75	.05	-55
1800	.20	140	4.14	1	.13	-94	.05	-22
	.28	22	4.13	-31	.14	-118	.22	-21



2707 Black Lake Place, Philadelphia, PA 19154

TEL 215-464-4000 ···· FAX 215-464-4001